LOGIC DEVICES INCORPORATED

L7C199
32K x 8 Static RAM

FEATURES

- 32K x 8 Static RAM with Chip Select Powerdown, Output Enable
- Auto-Powerdown™ Design
- Advanced CMOS Technology
- High Speed — to 15 ns maximum
- Low Power Operation
  Active: 350 mW typical at 35 ns
  Standby: 5 mW typical
- Data Retention at 2 V for Battery Backup Operation
- DSCC SMD No. 5962-88662
- Available 100% Screened to MIL-STD-883, Class B
- Plug Compatible with IDT71256, Cypress CY7C198/199
- Package Styles Available:
  - 28-pin Plastic DIP
  - 28-pin Ceramic DIP
  - 28-pin Plastic SOJ
  - 28-pin Ceramic Flatpack
  - 28-pin Ceramic LCC
  - 32-pin Ceramic LCC

DESCRIPTION

The **L7C199** is a high-performance, low-power CMOS static RAM. The storage circuitry is organized as 32,768 words by 8 bits per word. The 8 Data In and Data Out signals share I/O pins. This device is available in four speeds with maximum access times from 15 ns to 35 ns.

Inputs and outputs are TTL compatible. Operation is from a single +5 V power supply. Power consumption is 350 mW (typical) at 35 ns. Dissipation drops to 50 mW (typical) when the memory is deselected.

Two standby modes are available. Proprietary Auto-Powerdown™ circuitry reduces power consumption automatically during read or write accesses which are longer than the minimum access time, or when the memory is deselected. In addition, data may be retained in inactive storage with a supply voltage as low as 2 V. The L7C199 consumes only 150 µW (typical) , at 3 V, allowing effective battery backup operation.

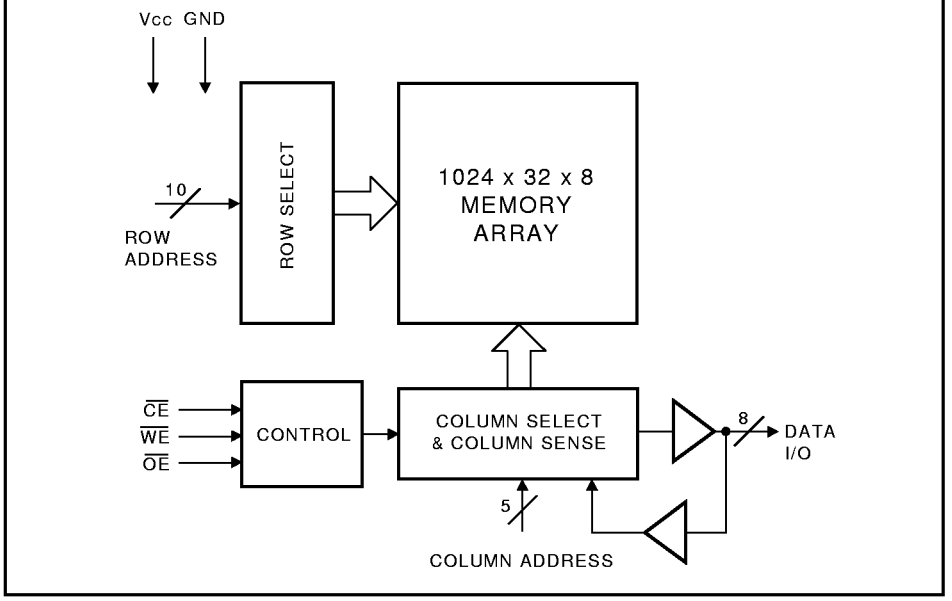
The L7C199 provides asynchronous (unclocked) operation with matching access and cycle times. An active-low Chip Enable and a three-state I/O bus with a separate Output Enable control simplify the connection of several chips for increased storage capacity.

Memory locations are specified on address pins A_0 through A_{14}. Reading from a designated location is accomplished by presenting an address and driving $\overline{CE}$ and $\overline{OE}$ LOW while $\overline{WE}$ remains HIGH. The data in the addressed memory location will then appear on the Data Out pins within one access time. The output pins stay in a high-impedance state when $\overline{CE}$ or $\overline{OE}$ is HIGH, or $\overline{WE}$ is LOW.

Writing to an addressed location is accomplished when the active-low $\overline{CE}$ and $\overline{WE}$ inputs are both LOW. Either signal may be used to terminate the write operation. Data In and Data Out signals have the same polarity.

Latchup and static discharge protection are provided on-chip. The L7C199 can withstand an injection current of up to 200 mA on any pin without damage.

L7C199 BLOCK DIAGRAM



Maximum Ratings *Above which useful life may be impaired (Notes 1, 2)*

Storage temperature	–65°C to +150°C
Operating ambient temperature	–55°C to +125°C
V_{CC} supply voltage with respect to ground	–0.5 V to +7.0 V
Input signal with respect to ground	–3.0 V to +7.0 V
Signal applied to high impedance output	–3.0 V to +7.0 V
Output current into low outputs	25 mA
Latchup current	> 200 mA

Operating Conditions *To meet specified electrical and switching characteristics*

Mode	Temperature Range (Ambient)	Supply Voltage
Active Operation, Commercial	0°C to +70°C	4.5 V ≤ V_{CC} ≤ 5.5 V
Active Operation, Industrial	–40°C to +85°C	4.5 V ≤ V_{CC} ≤ 5.5 V
Active Operation, Military	–55°C to +125°C	4.5 V ≤ V_{CC} ≤ 5.5 V
Data Retention, Commercial	0°C to +70°C	2.0 V ≤ V_{CC} ≤ 5.5 V
Data Retention, Industrial	–40°C to +85°C	2.0 V ≤ V_{CC} ≤ 5.5 V
Data Retention, Military	–55°C to +125°C	2.0 V ≤ V_{CC} ≤ 5.5 V

Electrical Characteristics *Over Operating Conditions (Note 5)*

			L7C199			
Symbol	Parameter	Test Condition	Min	Typ	Max	Unit
V_{OH}	Output High Voltage	V_{CC} = 4.5 V, I_{OH} = –4.0 mA	2.4			V
V_{OL}	Output Low Voltage	I_{OL} = 8.0 mA			0.4	V
V_{IH}	Input High Voltage		2.2		V_{CC} +0.3	V
V_{IL}	Input Low Voltage	(Note 3)	–3.0		0.8	V
I_{IX}	Input Leakage Current	Ground ≤ V_{IN} ≤ V_{CC}	–10		+10	µA
I_{OZ}	Output Leakage Current	(Note 4)	–10		+10	µA
I_{CC2}	V_{CC} Current, TTL Inactive	(Note 7)		10	20	mA
I_{CC3}	V_{CC} Current, CMOS Standby	(Note 8)		1	3	mA
I_{CC4}	V_{CC} Current, Data Retention	V_{CC} = 3.0 V (Notes 9, 10)		50	200	µA
C_{IN}	Input Capacitance	Ambient Temp = 25°C, V_{CC} = 5.0 V			5	pF
C_{OUT}	Output Capacitance	Test Frequency = 1 MHz (Note 10)			7	pF

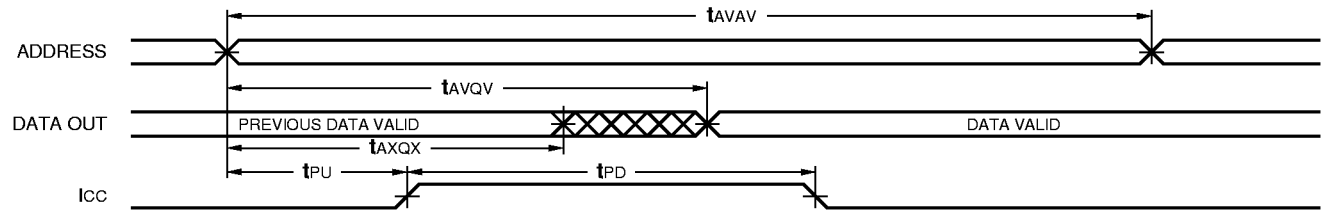
			L7C199-				
Symbol	Parameter	Test Condition	35	25	20	15	Unit
I_{CC1}	V_{CC} Current, Active	(Note 6)	95	120	145	180	mA

SWITCHING CHARACTERISTICS *Over Operating Range*

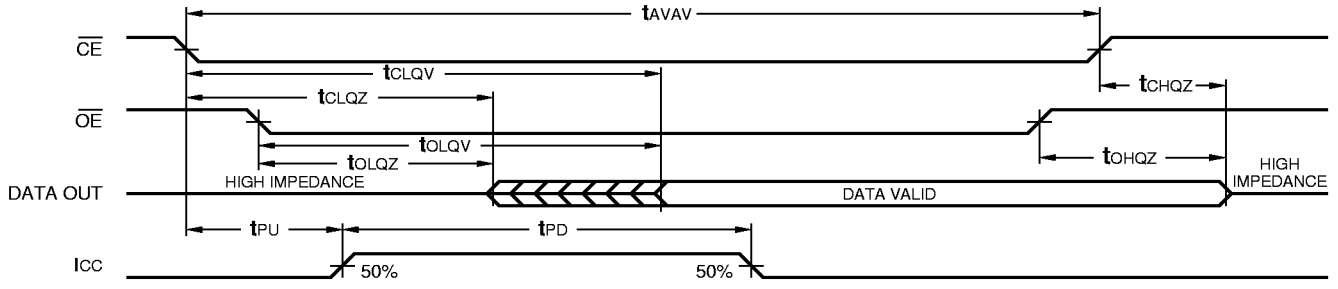
READ CYCLE *Notes 5, 11, 12, 22, 23, 24 (ns)*

		L7C199–							
		35		25		20		15	
Symbol	Parameter	Min	Max	Min	Max	Min	Max	Min	Max
t_{AVAV}	Read Cycle Time	35		25		20		15	
t_{AVQV}	Address Valid to Output Valid (Notes 13, 14)		35		25		20		15
t_{AXQX}	Address Change to Output Change	3		3		3		3	
t_{CLQV}	Chip Enable Low to Output Valid (Notes 13, 15)		35		25		20		15
t_{CLQZ}	Chip Enable Low to Output Low Z (Notes 20, 21)	3		3		3		3	
t_{CHQZ}	Chip Enable High to Output High Z (Notes 20, 21)		15		10		8		8
t_{OLQV}	Output Enable Low to Output Valid		15		12		10		8
t_{OLQZ}	Output Enable Low to Output Low Z (Notes 20, 21)	0		0		0		0	
t_{OHQZ}	Output Enable High to Output High Z (Notes 20, 21)		10		10		8		5
t_{PU}	Input Transition to Power Up (Notes 10, 19)	0		0		0		0	
t_{PD}	Power Up to Power Down (Notes 10, 19)		35		25		20		20
t_{CHVL}	Chip Enable High to Data Retention (Note 10)	0		0		0		0	

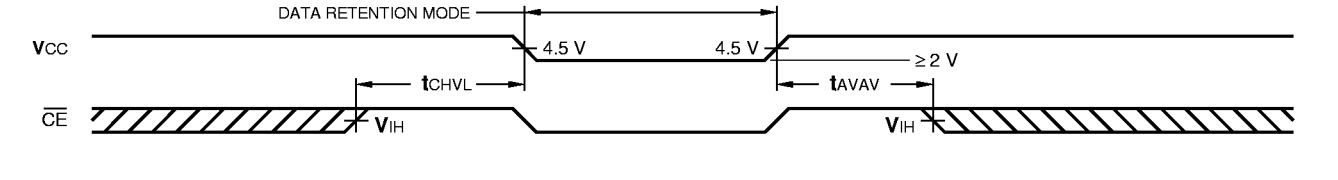
READ CYCLE — ADDRESS CONTROLLED *Notes 13, 14*



READ CYCLE — $\overline{CE}$/$\overline{OE}$ CONTROLLED *Notes 13, 15*



DATA RETENTION *Notes 9, 10*

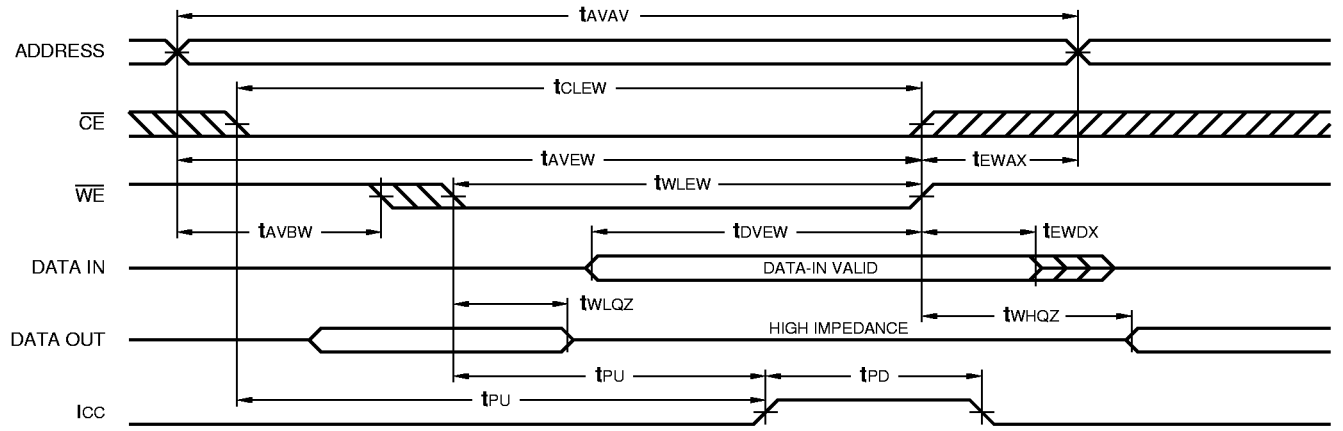


SWITCHING CHARACTERISTICS *Over Operating Range*

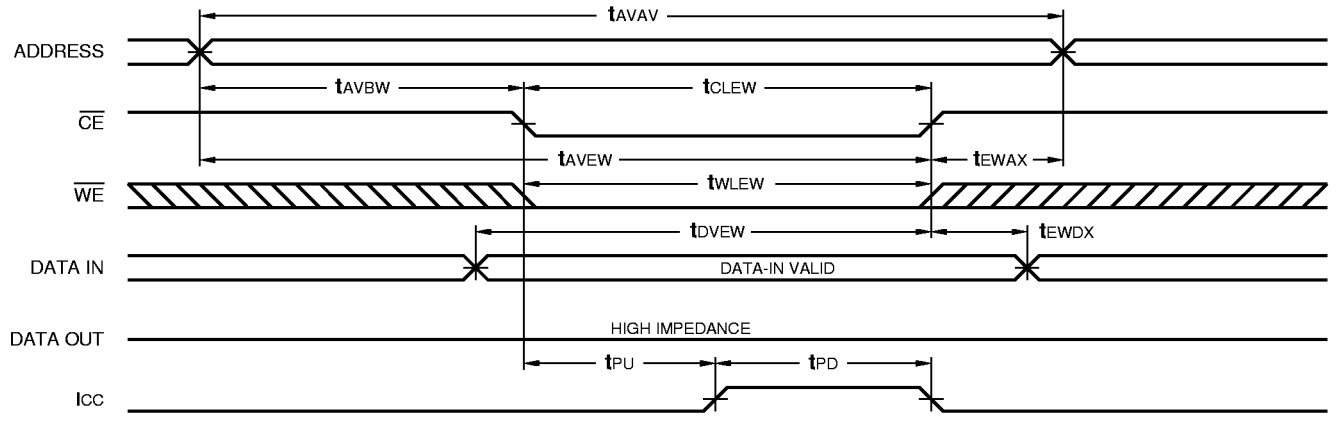
WRITE CYCLE *Notes 5, 11, 12, 22, 23, 24 (ns)*

		L7C199–							
		35		25		20		15	
Symbol	Parameter	Min	Max	Min	Max	Min	Max	Min	Max
t_{AVAV}	Write Cycle Time	25		20		20		15	
t_{CLEW}	Chip Enable Low to End of Write Cycle	25		15		15		12	
t_{AVBW}	Address Valid to Beginning of Write Cycle	0		0		0		0	
t_{AVEW}	Address Valid to End of Write Cycle	25		15		15		12	
t_{EWAX}	End of Write Cycle to Address Change	0		0		0		0	
t_{WLEW}	Write Enable Low to End of Write Cycle	20		15		15		12	
t_{DVEW}	Data Valid to End of Write Cycle	15		10		10		7	
t_{EWDX}	End of Write Cycle to Data Change	0		0		0		0	
t_{WHQZ}	Write Enable High to Output Low Z (Notes 20, 21)	0		0		0		0	
t_{WLQZ}	Write Enable Low to Output High Z (Notes 20, 21)		10		7		7		5

WRITE CYCLE — $\overline{WE}$ CONTROLLED *Notes 16, 17, 18, 19*



WRITE CYCLE — $\overline{CE}$ CONTROLLED *Notes 16, 17, 18, 19*



NOTES

1. Maximum Ratings indicate stress specifications only. Functional operation of these products at values beyond those indicated in the Operating Conditions table is not implied. Exposure to maximum rating conditions for extended periods may affect reliability of the tested device.

2. The products described by this specification include internal circuitry designed to protect the chip from damaging substrate injection currents and accumulations of static charge. Nevertheless, conventional precautions should be observed during storage, handling, and use of these circuits in order to avoid exposure to excessive electrical stress values.

3. This product provides hard clamping of transient undershoot. Input levels below ground will be clamped beginning at –0.6 V. A current in excess of 100 mA is required to reach –2.0 V. The device can withstand indefinite operation with inputs as low as –3 V subject only to power dissipation and bond wire fusing constraints.

4. Tested with GND ≤ V_{OUT} ≤ V_{CC}. The device is disabled, i.e., $\overline{CE}$ = V_{CC}.

5. A series of normalized curves is available to supply the designer with typical DC and AC parametric information for Logic Devices Static RAMs. These curves may be used to determine device characteristics at various temperatures and voltage levels.

6. Tested with all address and data inputs changing at the maximum cycle rate. The device is continuously enabled for writing, i.e., $\overline{CE}$ ≤ V_{IL}, $\overline{WE}$ ≤ V_{IL}. Input pulse levels are 0 to 3.0 V.

7. Tested with outputs open and all address and data inputs changing at the maximum read cycle rate. The device is continuously disabled, i.e., $\overline{CE}$ ≥ V_{IH}.

8. Tested with outputs open and all address and data inputs stable. The device is continuously disabled, i.e., $\overline{CE}$ = V_{CC}. Input levels are within 0.2 V of V_{CC} or GND.

9. Data retention operation requires that V_{CC} never drop below 2.0 V. $\overline{CE}$ must be ≥ V_{CC} – 0.2 V. All other inputs must meet V_{IN} ≥ V_{CC} – 0.2 V or V_{IN} ≤ 0.2 V to ensure full powerdown. For low power version (if applicable), this requirement applies only to $\overline{CE}$ and $\overline{WE}$; there are no restrictions on data and address.

10. These parameters are guaranteed but not 100% tested.

11. Test conditions assume input transition times of less than 3 ns, reference levels of 1.5 V, output loading for specified I_{OL} and I_{OH} plus 30 pF (Fig. 1a), and input pulse levels of 0 to 3.0 V (Fig. 2).

12. Each parameter is shown as a minimum or maximum value. Input requirements are specified from the point of view of the external system driving the chip. For example, t_{AVEW} is specified as a minimum since the external system must supply at least that much time to meet the worst-case requirements of all parts. Responses from the internal circuitry are specified from the point of view of the device. Access time, for example, is specified as a maximum since worst-case operation of any device always provides data within that time.

13. $\overline{WE}$ is high for the read cycle.

14. The chip is continuously selected ($\overline{CE}$ low).

15. All address lines are valid prior-to or coincident-with the $\overline{CE}$ transition to active.

16. The internal write cycle of the memory is defined by the overlap of $\overline{CE}$ active and $\overline{WE}$ low. All three signals must be active to initiate a write. Any signal can terminate a write by going inactive. The address, data, and control input setup and hold times should be referenced to the signal that becomes active last or becomes inactive first.

17. If $\overline{WE}$ goes low before or concurrent with the latter of $\overline{CE}$ going active, the output remains in a high impedance state.

18. If $\overline{CE}$ goes inactive before or concurrent with $\overline{WE}$ going high, the output remains in a high impedance state.

19. Powerup from I_{CC2} to I_{CC1} occurs as a result of any of the following conditions:

a. Falling edge of $\overline{CE}$.

b. Falling edge of $\overline{WE}$ ($\overline{CE}$ active).

c. Transition on any address line ($\overline{CE}$ active).

d. Transition on any data line ($\overline{CE}$, and $\overline{WE}$ active).

The device automatically powers down from I_{CC1} to I_{CC2} after t_{PD} has elapsed from any of the prior conditions. This means that power dissipation is dependent on only cycle rate, and is not on Chip Select pulse width.

20. At any given temperature and voltage condition, output disable time is less than output enable time for any given device.

21. Transition is measured ±200 mV from steady state voltage with specified loading in Fig. 1b. This parameter is sampled and not 100% tested.

22. All address timings are referenced from the last valid address line to the first transitioning address line.

23. $\overline{CE}$ or $\overline{WE}$ must be inactive during address transitions.

24. This product is a very high speed device and care must be taken during testing in order to realize valid test information. Inadequate attention to setups and procedures can cause a good part to be rejected as faulty. Long high inductance leads that cause supply bounce must be avoided by bringing the V_{CC} and ground planes directly up to the contactor fingers. A 0.01 µF high frequency capacitor is also required between V_{CC} and ground. To avoid signal reflections, proper terminations must be used.

FIGURE 1a.

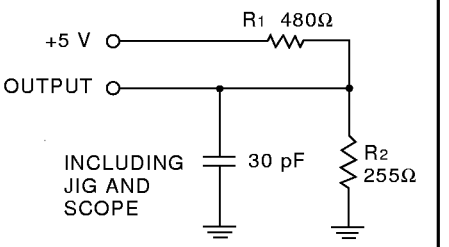


FIGURE 1b.

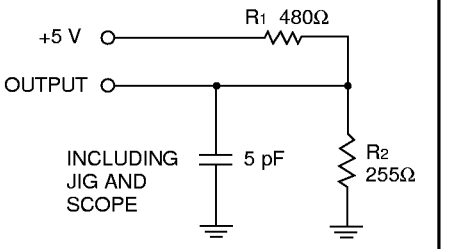
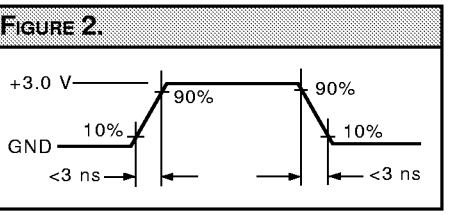
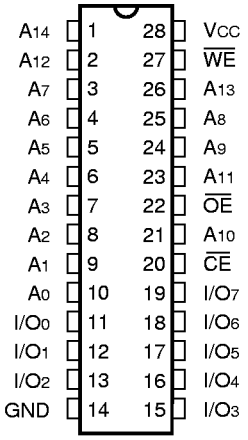


FIGURE 2.

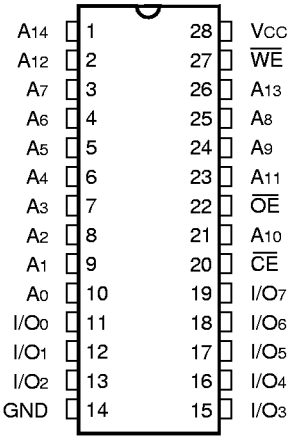


ORDERING INFORMATION

28-pin — 0.3" wide



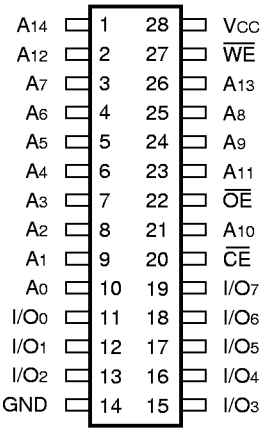
28-pin — 0.6" wide



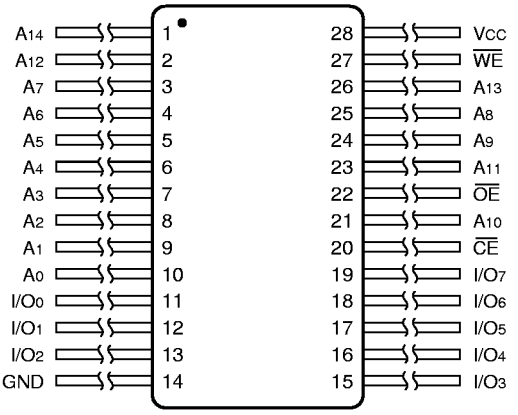
Speed	Plastic DIP (P10)	Ceramic DIP (C5)	Plastic DIP (P9)	Ceramic DIP (C6)
	0°C to +70°C — Commercial Screening			
25 ns	L7C199PC25	L7C199CC25	L7C199NC25	L7C199IC25
20 ns	L7C199PC20	L7C199CC20	L7C199NC20	L7C199IC20
15 ns	L7C199PC15	L7C199CC15	L7C199NC15	L7C199IC15
	–40°C to +85°C — Commercial Screening			
25 ns	L7C199PI25		L7C199NI25	
20 ns	L7C199PI20		L7C199NI20	
15 ns	L7C199PI15		L7C199NI15	
	–55°C to +125°C — Commercial Screening			
35 ns		L7C199CM35		L7C199IM35
25 ns		L7C199CM25		L7C199IM25
20 ns		L7C199CM20		L7C199IM20
	–55°C to +125°C — MIL-STD-883 Compliant			
35 ns		L7C199CMB35		L7C199IMB35
25 ns		L7C199CMB25		L7C199IMB25
20 ns		L7C199CMB20		L7C199IMB20

ORDERING INFORMATION

28-pin — 0.3" wide



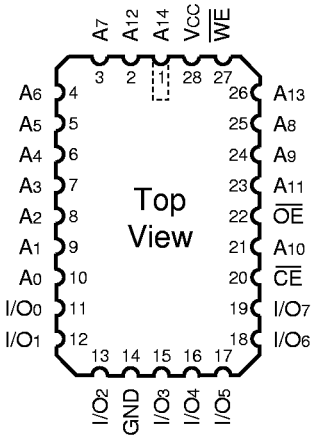
28-pin



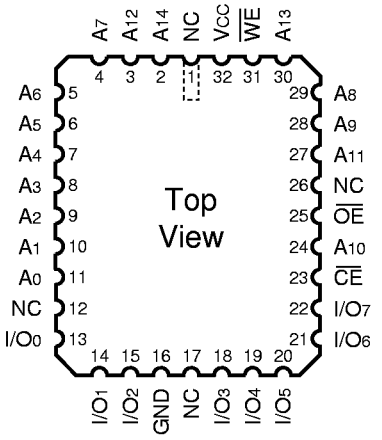
Speed	Plastic SOJ (W2)	Ceramic Flatpack (M2)
	0°C to +70°C — Commercial Screening	
25 ns	L7C199WC25	L7C199MC25
20 ns	L7C199WC20	L7C199MC20
15 ns	L7C199WC15	L7C199MC15
	–40°C to +85°C — Commercial Screening	
25 ns	L7C199WI25	
20 ns	L7C199WI20	
15 ns	L7C199WI15	
	–55°C to +125°C — Commercial Screening	
35 ns		L7C199MM35
25 ns		L7C199MM25
20 ns		L7C199MM20
	–55°C to +125°C — MIL-STD-883 Compliant	
35 ns		L7C199MMB35
25 ns		L7C199MMB25
20 ns		L7C199MMB20

ORDERING INFORMATION

28-pin



32-pin



Speed	Ceramic Leadless Chip Carrier (K5)	Ceramic Leadless Chip Carrier (K7)
	0°C to +70°C — Commercial Screening	
25 ns	L7C199KC25	L7C199TC25
20 ns	L7C199KC20	L7C199TC20
15 ns	L7C199KC15	L7C199TC15
	–40°C to +85°C — Commercial Screening	
25 ns		
20 ns		
15 ns		
	–55°C to +125°C — Commercial Screening	
35 ns	L7C199KM35	L7C199TM35
25 ns	L7C199KM25	L7C199TM25
20 ns	L7C199KM20	L7C199TM20
	–55°C to +125°C — MIL-STD-883 Compliant	
35 ns	L7C199KMB35	L7C199TMB35
25 ns	L7C199KMB25	L7C199TMB25
20 ns	L7C199KMB20	L7C199TMB20